

PROCESSOR TYPE PDP-11/45

M8105-00001 CODE: D CS: B ETCH: C
MAR-72 - PROBLEM: Etch errors on revision "B" artwork of M8105.
CORRECTION: Correct etch and digitize board.
In-plant effectivity -02 phase-in

ETCH: D

M8105-00002 CODE: D CS: C
MAY-72 - CORRECTION: Change disable gate in priority arbitration.
In-plant effectivity -03 rework immediately

M8105-B0003 CODE: DF CS: D ETCH: E
AUG-72 - PROBLEM 1: PIRQ LEV 1 request locks out "T" bit if PSW
priority is at LEV 1.
CORRECTION 1: Remove PIR LEV 1 from inhibiting "T" bit by cutting
etch from E50 pin 5 to E46 pin 6 and adding jumper from E50 pin 5 to
E50 pin 4.
CORRECTION 2: Correct print on TCMF.

NOTE: Existing diagnostics do not test the failing condition; a test pro-
gram is included in the FCO.
In-plant effectivity -03 rework immediately, 9/11/72
Field effectivity -Rework all M8105's in PDP-11/45 systems.
(Time To Install And Test .8 Hour.) (Kit Contents -FCO/Prints)

M8105-00004 CODE: D CS: E
DEC-72 - PROBLEM: Not necessary to have 74S74-45 in E37.
CORRECTION: Replace E37 with 74S74.
In-plant effectivity -02 phase-in 1/1/73.

M8105-D0005 CODE: F CS: F
MAR-73 - PROBLEM: Parity errors are time consuming to detect
through vector 4.
CORRECTION: Make parity trap to 114.

NOTE: The following FCO's must be installed in total to fully implement
core parity: M8100-D0003, M8103-D0005, M8105-D0005, M8106-D0007, KB11A-
D0015, and M8106-D0008. Each of these related FCO's may be installed
separately; each FCO relies upon the others only to fully implement pa-
rity. Note that MS11-B/C semiconductor parity memories with etch revi-
sion "B" M8110's will not function properly with the above FCO's in-
stalled. A new M8110 is being designed to allow proper operation with the
FCO's installed.
In-plant effectivity -02 phase-in to Module Production March 1, 1973. Re-
work parity machines in Systems Checkout area and parity systems as re-
quired.
Field effectivity -Rework all M8105's in core parity PDP-11/45's
(Time To Install And Test 1.5 Hours.) (Kit Contents -FCO/Prints And
Parts)

M8105-C0006 CODE: F CS: H
JUN-73 - PROBLEM: References to internal registers cause unnecessary
data to be put on the UNIBUS.
CORRECTION: Disable TMCD XX BYTE EN H until master sync is as-
serted. The rework procedure is as follows: Cut etch from E15 pin 2, side
2; cut etch from third plated thru hole left of E05 pin 1, side 1; jumper
plated thru hole connected to E09 pin 7 to plated thru hole right of E09
pin 7; jumper plated thru hole connected to E09 pin 1 to E16 pin 2; jum-
per plated through hole connected to E09 pin 2 to E07 pin 2; jumper E15
pin 2 to E15 pin 5; jumper plated thru hole connected to E09 pin 3 to
third plated thru hole left of E01-05; insert IC type 74S00 in spare IC slot
E9.
In-plant effectivity -03 * -Rework in module production and for test area
immediately. Rework basics, systems, and field as needed. All shipments
after August 6, 1973 will have this FCO.
Field effectivity -Rework CS revision "F" and earlier M8105's shipped
prior to August 6, 1973.
(Time To Install And Test 1.0 Hour.) (Kit Contents -FCO/Prints And
Parts)

M8105-C0007 CODE: F CS: J
OCT-73 - PROBLEM: The processor can hang in T2 and pause without
UBCA GET BUS 1 H. This is because of a glitch on RACH DIS BUST L.
If it is an MOS or bipolar system, it could get invalid address calcu-
lation.
CORRECTION: Create ROM decode of BUST H on the M8103 board. Jum-
per the new source of BUST H into M8105 logic. The rework procedure is
as follows: Cut etch from E34 pin 08 on side 1. Jumper plated thru hole
connected to pin CT2 to plated thru hole connected to pin DU2.

NOTE: This FCO must be installed in conjunction with FCO M8103-C0006.
In-plant effectivity -Rework in Module Production and Basic CPU Line.
Rework in systems area and acceptance area only as necessary. Rework
all boards in-plant as of November 1, 1973.
Field effectivity -Rework all M8105's in systems with MOS or bipolar
memory and in systems that cannot be margined at 140 nsec.
(Time To Install And Test 1.0 Hour.) (Kit Contents -FCO/Prints)

M8105-00008 CODE: D CS: K ETCH: F
NOV-73 - PROBLEM: MOS memory systems with KT11-C could pick up
bits in MOS memory; the problem only occurs during KT11-C abort traps.
CORRECTION: Issue TMCE BEND CLRL to MOS control during the
pause ROM cycle.
In-plant effectivity -Do not rework any existing boards. Phase-in change to
create new etch revision "F" board by March 4, 1974.